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(54) **METHOD OF MANUFACTURING  
SEMICONDUCTOR ELEMENT**

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**ABSTRACT**

A method of manufacturing a semiconductor element includes: providing a structure including: a semiconductor structure, a resin member, and a first insulation film; forming a cover member disposed continuously on a portion of the first insulation film; forming a resist film on the cover member, and removing a portion of the cover member; removing a portion of the first insulation film and a portion of the resin member; and removing a remaining portion of the cover member.

